

ETCHING METHOD AND ETCHING PROCESSING APPARATUS

ABSTRACT

An etching method of a substrate includes (a) providing a substrate on a substrate support inside a chamber, the substrate including a first region having a multilayer film in which a silicon oxide film and a silicon nitride film are alternately stacked and a second region having a monolayer silicon oxide film; and (b) etching the substrate with plasma generated from a first processing gas that includes a hydrofluorocarbon gas, wherein the hydrofluorocarbon gas includes a first hydrofluorocarbon gas represented by $C_xH_yF_z$ (x represents an integer of 2 or more, and y and z represent an integer of 1 or more) and having an unsaturated bond.

[Figure 6]